ALPHA & OMEGA SEMICONDUCTOR

AO4413

30V P-Channel MOSFET

General Description

• The AO4413 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.

• RoHS and Halogen-Free Compliant

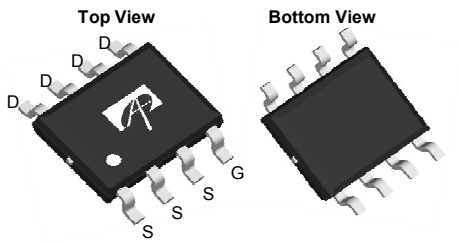
Product Summary

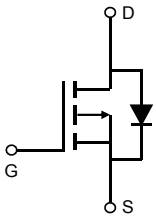
V_{DS}	-30V
I_D (at V_{GS}=-20V)	-15A
$R_{DS(ON)}$ (at V_{GS}=-20V)	< 7mΩ
$R_{DS(ON)}$ (at V_{GS} = -10V)	< 8.5mΩ

100% UIS Tested
100% R_g Tested

Green Product

SOIC-8





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current	T_A=25°C	I_D	-15	A
	T_A=70°C		-12.8	
Pulsed Drain Current [C]		I_{DM}	-120	
Avalanche Current [C]		I_{AS}, I_{AR}	50	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	125	mJ
Power Dissipation [B]	T_A=25°C	P_D	3.1	W
	T_A=70°C		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	31	40	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		59	75	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	16	24	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±25V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-1.5	-2.5	-3.5	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V	-120			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-20V, I_D=-15A		5.3	7	mΩ
		T_J=125°C		7.5	9	
		V_{GS}=-10V, I_D=-15A		6.4	8.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-15A		35		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz	2310	2890	3500	pF
C_{oss}	Output Capacitance		410	585	760	pF
C_{rss}	Reverse Transfer Capacitance		280	470	660	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	1.9	3.8	5.7	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-15A	40	51	61	nC
Q_{gs}	Gate Source Charge		10	12	14	nC
Q_{gd}	Gate Drain Charge		10	16	22	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=1.0Ω, R_{GEN}=3Ω		16		ns
t_r	Turn-On Rise Time			12		ns
$t_{D(off)}$	Turn-Off DelayTime			45		ns
t_f	Turn-Off Fall Time			22		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-15A, dI/dt=100A/µs	14	18	22	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-15A, dI/dt=100A/µs	9	11	13	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

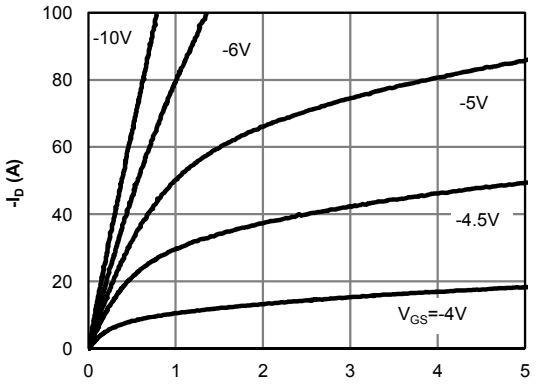


Fig 1: On-Region Characteristics (Note E)

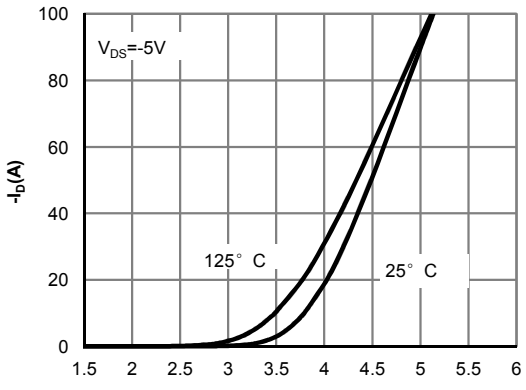


Figure 2: Transfer Characteristics (Note E)

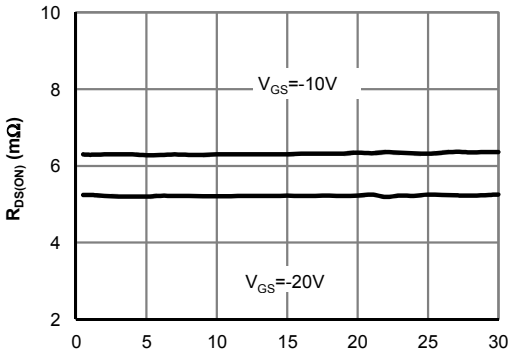


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

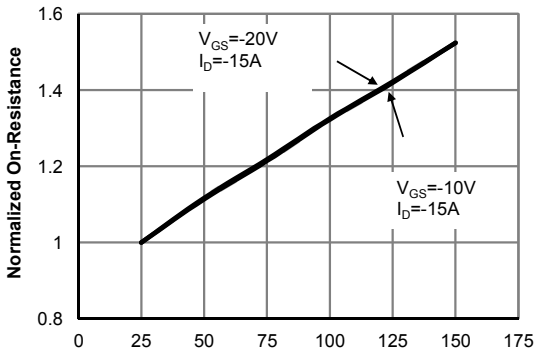


Figure 4: On-Resistance vs. Junction Temperature (Note E)

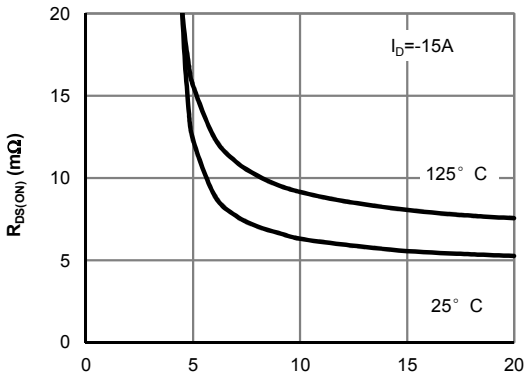


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

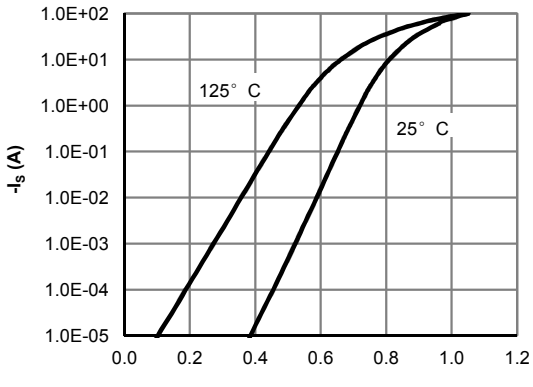


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

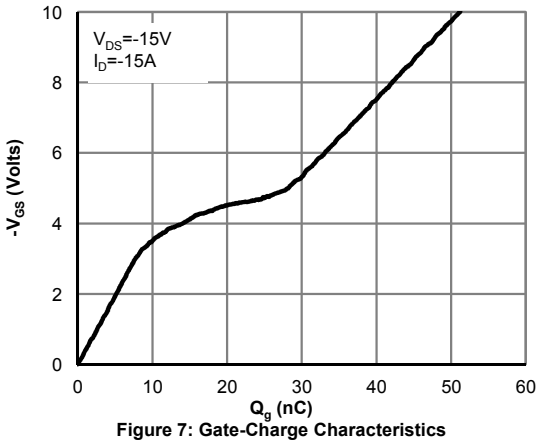


Figure 7: Gate-Charge Characteristics

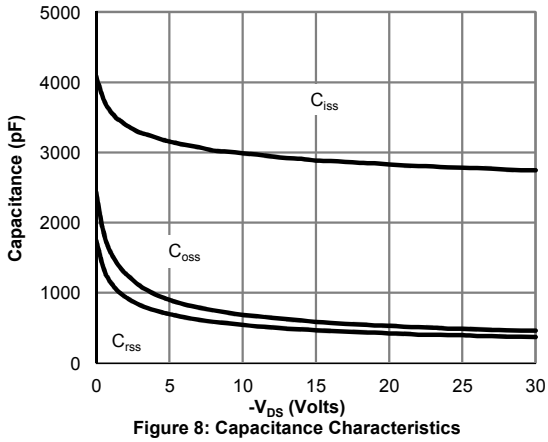


Figure 8: Capacitance Characteristics

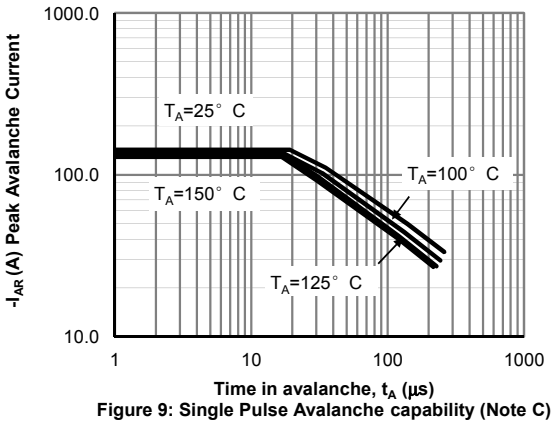


Figure 9: Single Pulse Avalanche capability (Note C)

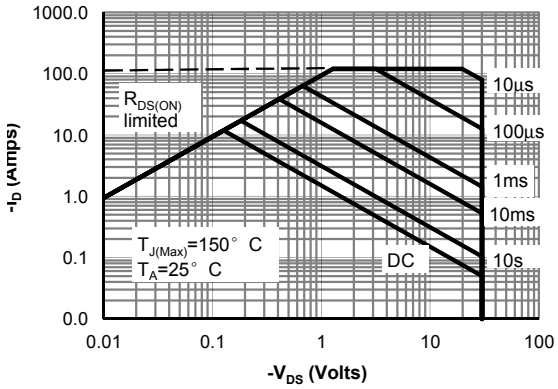


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

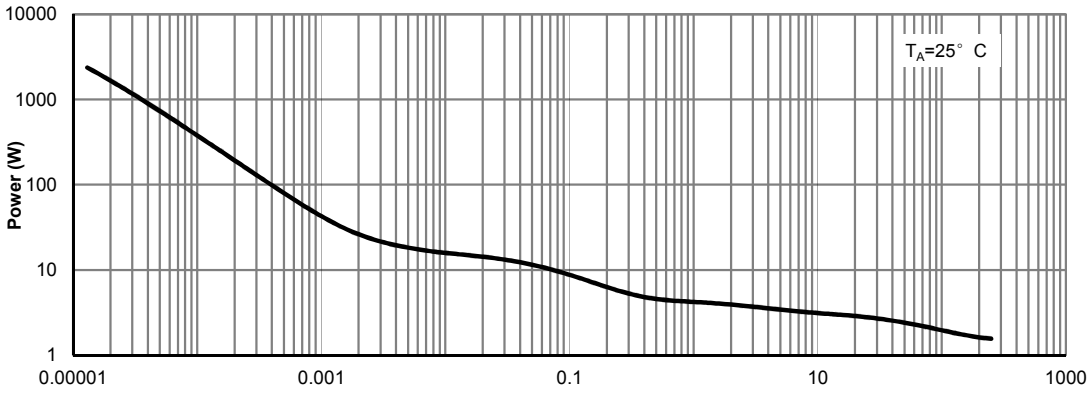


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

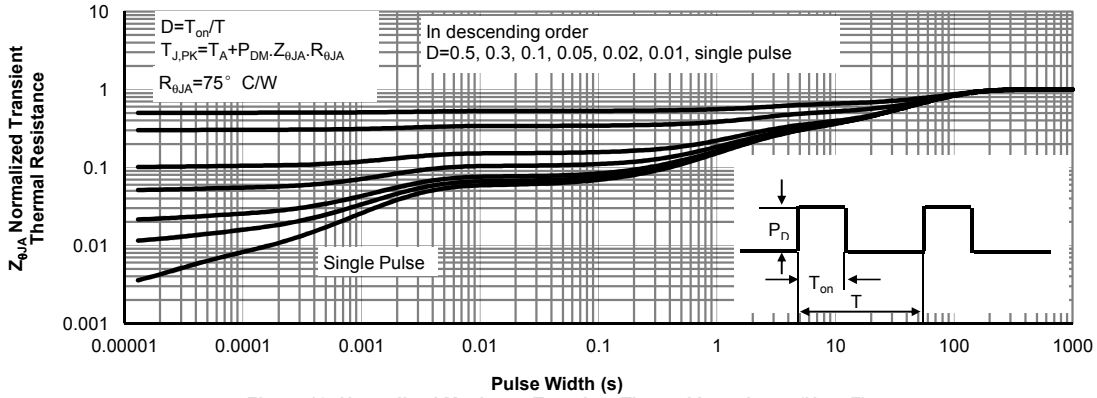
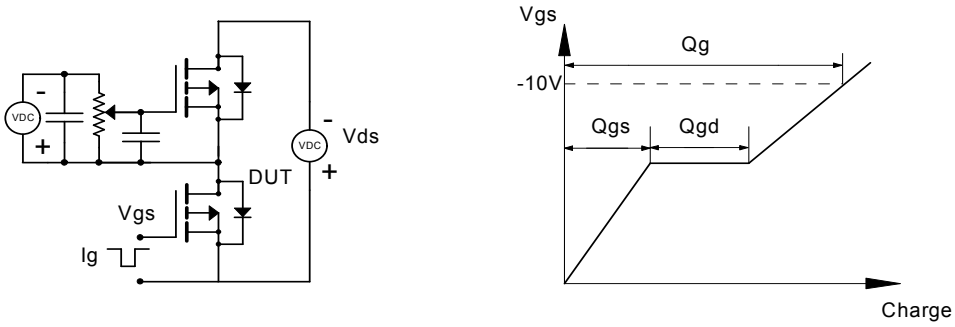
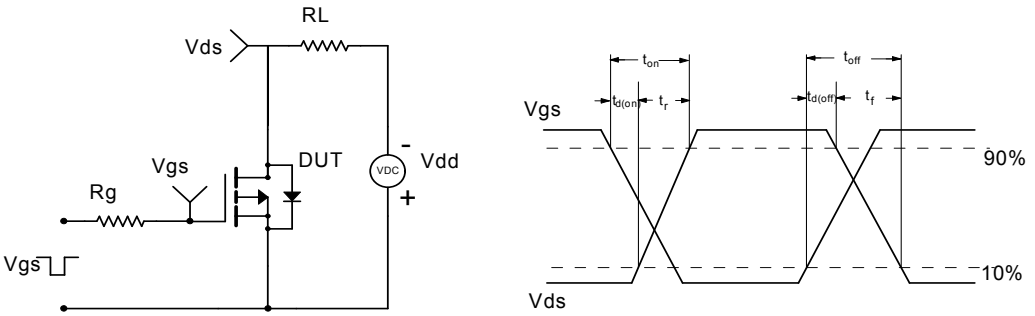


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

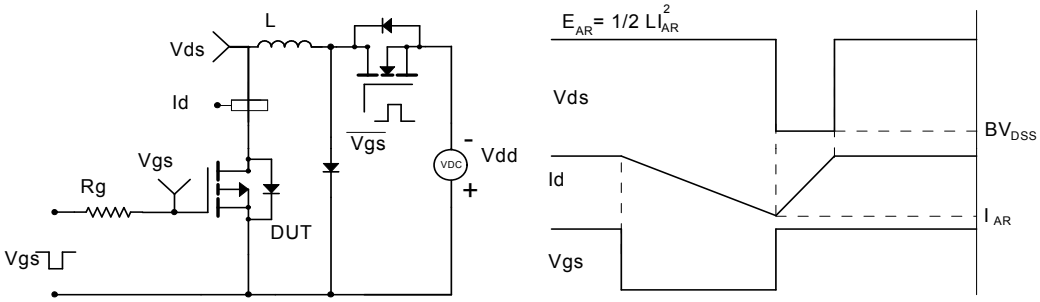
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms